

What is claimed is:

- 1 1. A device for use in an imaging system comprising:
2 a direct conversion detector element configured to convert x-ray
3 photons into electric current, said direct conversion detector element
4 comprising:
5 a cathode surface;
6 an anode surface having a plurality of anode side edges; and
7 a plurality of detector side surfaces connecting said cathode
8 surface to said anode surface, said plurality of detector side surfaces each
9 having a detector depth ;
10 a pixel array assembly positioned on said anode surface, said
11 pixel array assembly including a plurality of pixel side edges, each of said
12 plurality of pixel side edges immediately adjacent one of said anode side edges;
13 a guard ring mounted around said plurality of detector side
14 surfaces, said guard ring including an upper ring edge, a lower ring edge, and a
15 ring outer surface including a guard ring height.
- 1 2. A device as in claim 1 further comprising:
2 a voltage source in communication with said guard ring, said
3 voltage source biasing said guard ring with a bias voltage.
- 1 3. A device as in claim 1 wherein said upper ring edge and
2 said lower ring edge are remotely positioned from said cathode surface and said
3 anode surface.
- 1 4. A device as in claim 1 wherein said ring outer surface is
2 coplanar with said pixel side edges.
- 1 5. A device as in claim 1 wherein said ring outer surface is
2 coplanar with said plurality of detector side surfaces.

1 6. A device as in claim 1 wherein said direct conversion
2 detector element comprises amorphous selenium.

1 7. A device as in claim 1 wherein said pixel array assembly
2 comprises a room temperature semiconductor.

1 8. A device as in claim 1 wherein said direct conversion
2 detector element comprises a CdTe detector.

1 9. A device as in claim 1 wherein guard ring height is 50%
2 or less of said detector depth.

1 10. A device as in claim 1 wherein said upper ring edge and
2 said lower ring edge are positioned closer to said anode surface than said
3 cathode surface.

1 11. An imaging system comprising:
2 an x-ray source;
3 a detector array comprising a plurality of direct conversion
4 detector elements configured to convert x-ray photons into electric current, each
5 of said plurality of direct conversion detector elements comprising:
6 a cathode surface;
7 an anode surface having a plurality of anode side edges; and
8 a plurality of detector side surfaces connecting said cathode
9 surface to said anode surface, said plurality of detector side surfaces each
10 having a detector depth ;
11 a pixel array assembly positioned on said anode surface, said
12 pixel array assembly including a plurality of pixel side edges;
13 a guard ring mounted around said plurality of detector side
14 surfaces, said guard ring including an upper ring edge, a lower ring edge, and a
15 ring outer surface including a guard ring height, said ring outer surface
16 positioned coplanar with said pixel side edges.

1 12. An imaging system as described in claim 11 wherein
2 each of said plurality of pixel side edges is positioned immediately adjacent one
3 of said anode side edges.

1 13. An imaging system as in claim 11 further comprising:
2 a voltage source in communication with said guard ring, said
3 voltage source biasing said guard ring with a bias voltage.

1 14. An imaging system as in claim 11 wherein said upper
2 ring edge and said lower ring edge are remotely positioned from said cathode
3 surface and said anode surface.

1 15. An imaging system as in claim 11, wherein said ring
2 outer surface is coplanar with said plurality of detector side surfaces.

1 16. An imaging system as in claim 11 wherein said guard
2 ring is coated on said plurality of detector side surfaces such that said guard ring
3 is substantially coplanar with said plurality of detector side surfaces.

1 17. A method of improving the performance of peripheral
2 pixel elements positioned on an anode surface of a direct conversion detector
3 element, the direct conversion detector element having a cathode surface and a
4 plurality of detector side surfaces, comprising:
5 applying a guard ring around said plurality of detector side
6 surfaces, said guard ring applied coplanar to said peripheral pixel elements.

1 18. A method as described in claim 17, further comprising:
2 applying a bias voltage to said guard ring.

1 19. A method as described in claim 17, further comprising:
2 adjusting a guard ring height of said guard ring to maximize the
3 performance of the peripheral pixel elements.

1 20. A method as described in claim 17, further comprising:

- 2 adjusting a guard ring position along a detector depth to
- 3 maximize the performance of the peripheral pixel elements.